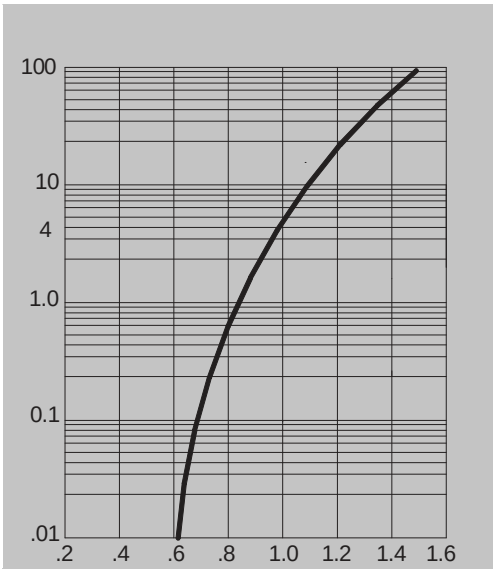
ð Rating to 1000V PRV

ð Surge 0.0006 Tw 0.791 0.036 Td[(S)39cs 0.1Tw 0.791 0G4691.9Tc4(oa9cs 0d Td[(i)18(cs 0t)96(h)(er4(i)078)96(h)o A)Tj/TT3to 1000V PR

		KBJ 8A	KBJ 8B	KBJ 8D	KBJ 8G	KBJ 8J	KBJ 8K	KBJ 8M	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forw ard Output current @T_A=110℃	$I_{F(AV)}$				8.0				A
Peak forw ard surge current 8.3ms single half-sine-w ave superimposed on rated load	I_{FSM}				200.0				A
Maximum instantaneous forw ard voltage at 4.0 A	V_F				1.0				V
Maximum reverse current @T_A=25℃									μA
at rated DC blocking voltage @T_A=100℃					1.0				mA
Typical junction capacitance per element	C_J								pF
Typical thermal resistance	$R_{\theta JC}$								℃/W
Operating junction temperature range	T_J								℃
Storage temperature range	T_{STG}								℃

2.Device mounted on 300mm X 300mm X 1.6mm cu Plate heatsink.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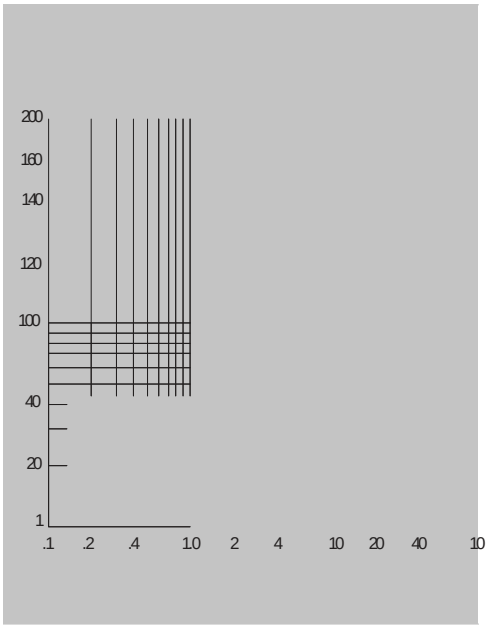
0.1
.01
.2
.4
.6
.8
1.0
1.2
1.4
1.6


200
160
140
120
100
40
20
1
.1
.2
.4
1.0
2
4
10
20
40
10